BUK6Y24-40P

40 V, P-channel Trench MOSFET

9 April 2020 Product data sheet

1. General description

P-channel enhancement mode MOSFET in an LFPAK56 (Power SO8) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

This product has been designed and qualified to AEC-Q101 standard for use in high-performance automotive applications such as reverse battery protection.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for thermally demanding environments due to 175 °C rating
- Trench MOSFET technology
- AEC-Q101 qualified

3. Applications

- Reverse battery protection
- Power management
- High-side load switch
- Motor drive

4. Quick reference data

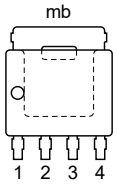
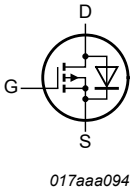
Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-	-40	V
V_{GS}	gate-source voltage		[1]	-20	-	20	V
I_D	drain current	V_{GS} = -10 V; T_{mb} = 25 °C		-	-	-39	A
P_{tot}	total power dissipation	T_{mb} = 25 °C		-	-	66	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -8.2 A; T_j = 25 °C		-	19	24	mΩ

[1] V_{GS} = -20 V/+5 V according AEC-Q101 at T_j = 175 °C; V_{GS} = -20 V/+20 V according AEC-Q101 at T_j = 150 °C

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 **LFPAK56; Power-SO8 (SOT669)**	 *017aaa094*
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6Y24-40P	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK6Y24-40P	6Y2440P

8. Limiting values

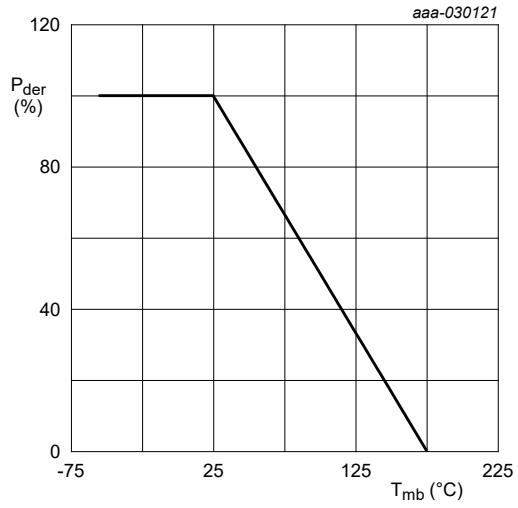
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T_j = 25 °C		-	-40	V
V_{GS}	gate-source voltage		[1]	-20	20	V
I_D	drain current	V_{GS} = -10 V; T_{mb} = 25 °C		-	-39	A
		V_{GS} = -10 V; T_{mb} = 100 °C		-	-27	A
I_{DM}	peak drain current	single pulse; $t_p \leq$ 10 µs; T_{mb} = 25 °C		-	-155	A
P_{tot}	total power dissipation	T_{mb} = 25 °C		-	66	W
T_j	junction temperature			-55	175	°C
T_{amb}	ambient temperature			-55	175	°C
T_{stg}	storage temperature			-65	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C		-	-39	A
I_{SM}	peak source current	single pulse; $t_p \leq$ 10 µs; T_{mb} = 25 °C		-	-155	A
ESD maximum rating						
V_{ESD}	electrostatic discharge voltage	HBM	[2]	-	500	V
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -4.6 A; DUT in avalanche (unclamped)		-	54	mJ

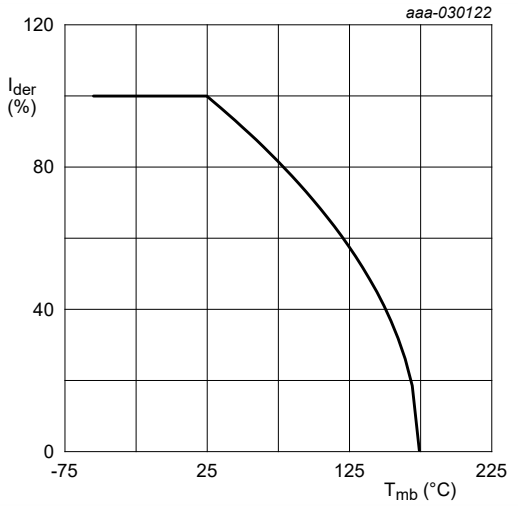
[1] V_{GS} = -20 V/+5 V according AEC-Q101 at T_j = 175 °C; V_{GS} = -20 V/+20 V according AEC-Q101 at T_j = 150 °C

[2] Measured between all pins.



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\ \%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25°C)}} \times 100\ \%$$

Fig. 2. Normalized continuous drain current as a function of mounting base temperature

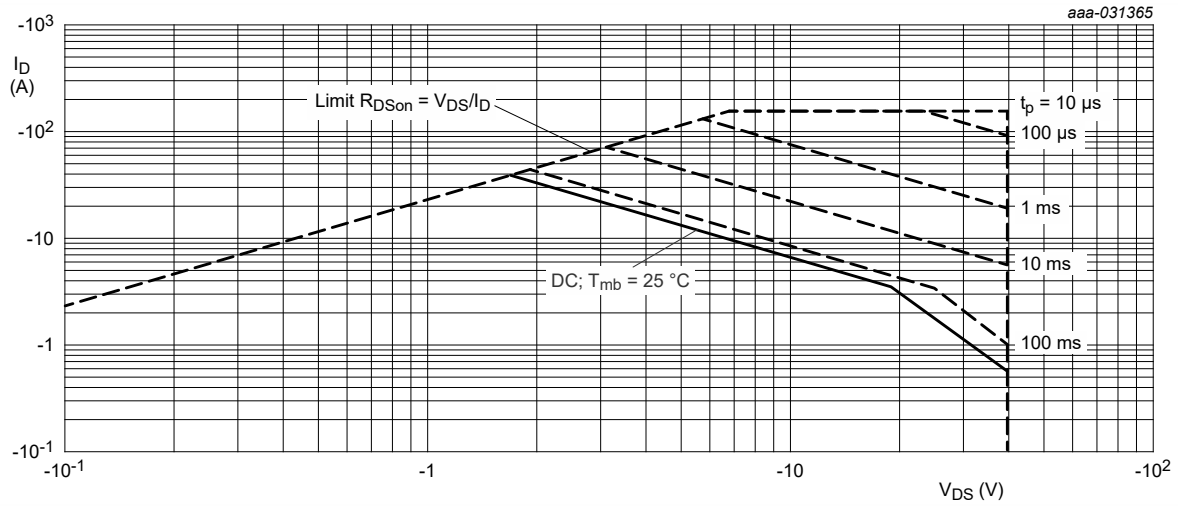


Fig. 3. Safe operating area; junction to mounting base; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base			-	1.8	2.3	K/W

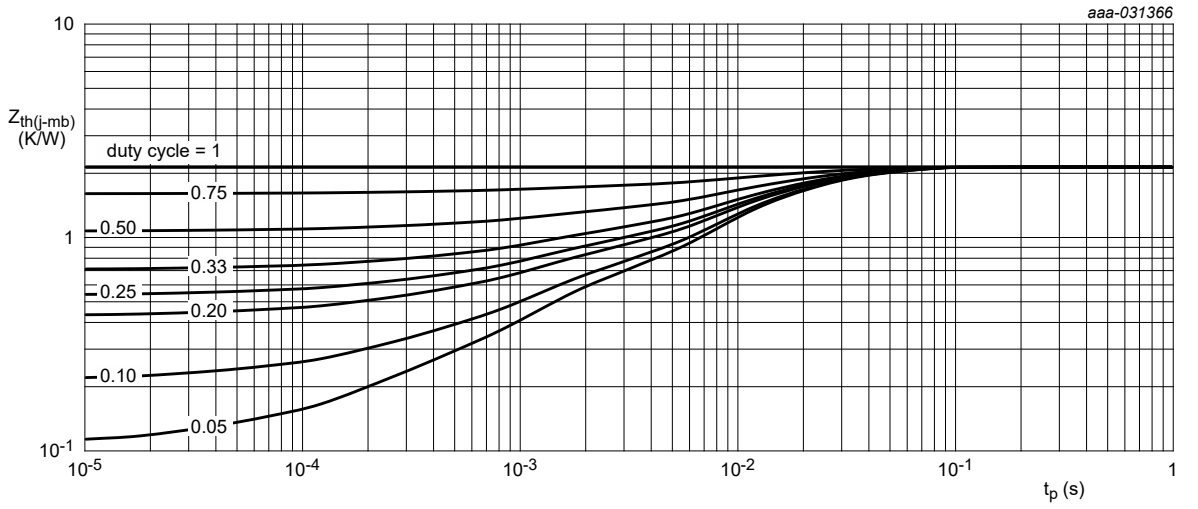
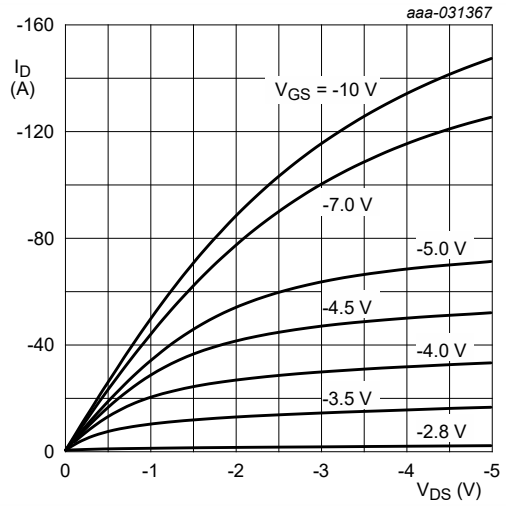


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

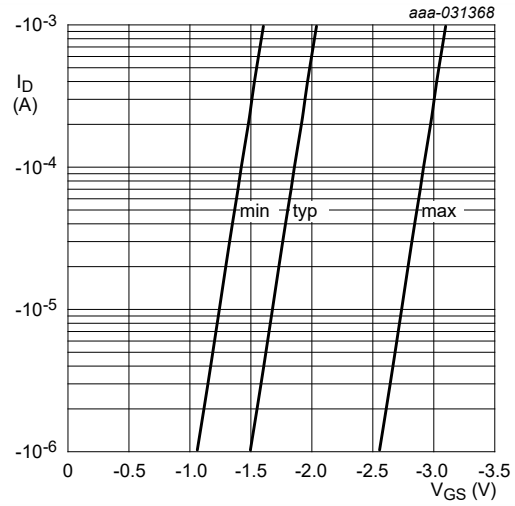
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = -250 µA; V_{GS} = 0 V; T_j = 25 °C		-40	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 µA; V_{DS}=V_{GS}; T_j = 25 °C		-1.5	-2	-3	V
I_{DSS}	drain leakage current	V_{DS} = -40 V; V_{GS} = 0 V; T_j = 25 °C		-	-	-1	µA
		V_{DS} = -40 V; V_{GS} = 0 V; T_j = 125 °C		-	-	-10	µA
I_{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	-100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	-	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = -10 V; I_D = -8.2 A; T_j = 25 °C		-	19	24	mΩ
		V_{GS} = -10 V; I_D = -8.2 A; T_j = 175 °C		-	35	44	mΩ
		V_{GS} = -4.5 V; I_D = -5.6 A; T_j = 25 °C		-	30	50	mΩ
g_{fs}	forward transconductance	V_{DS} = -10 V; I_D = -4 A; T_j = 25 °C		-	14	-	S
R_G	gate resistance	f = 1 MHz		-	11	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	V_{DS} = -20 V; I_D = -8.2 A; V_{GS} = -10 V; T_j = 25 °C		-	23	35	nC
Q_{GS}	gate-source charge			-	4	-	nC
Q_{GD}	gate-drain charge			-	5	-	nC
C_{iss}	input capacitance	V_{DS} = -20 V; f = 1 MHz; V_{GS} = 0 V; T_j = 25 °C		-	1250	-	pF
C_{oss}	output capacitance			-	184	-	pF
C_{rss}	reverse transfer capacitance			-	100	-	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = -20 V; I_D = -8.2 A; V_{GS} = -10 V; $R_{G(ext)}$ = 6 Ω; T_j = 25 °C		-	7	-	ns
t_r	rise time			-	25	-	ns
$t_{d(off)}$	turn-off delay time			-	50	-	ns
t_f	fall time			-	450	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = -39 A; V_{GS} = 0 V; T_j = 25 °C		-	-0.7	-1.2	V
t_{rr}	reverse recovery time	I_S = -39 A; dI_S/dt = 100 A/µs; V_{GS} = -10 V; V_{DS} = -20 V; T_j = 25 °C		-	21	-	ns
Q_r	recovered charge			-	18	-	nC



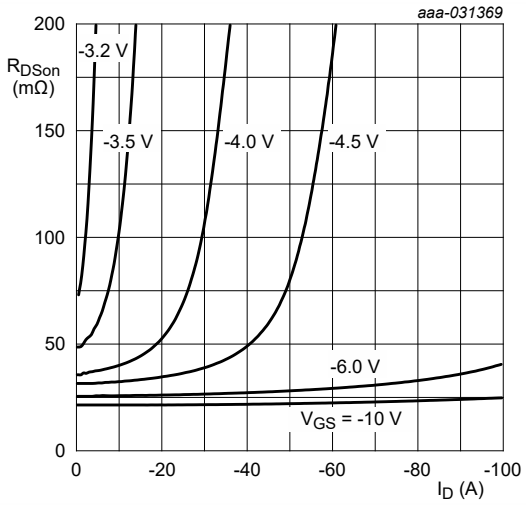
T_j = 25 °C

Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



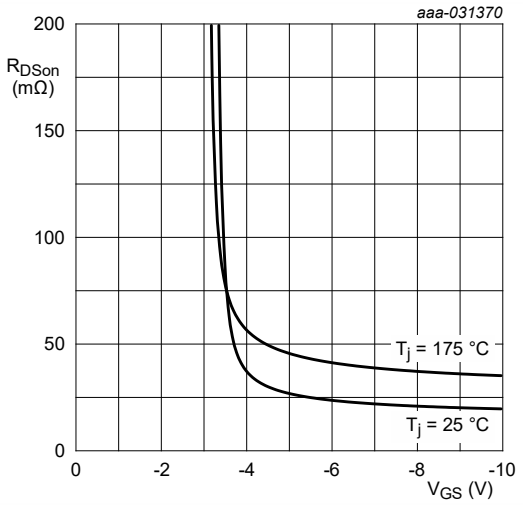
V_{DS} = -5 V; T_j = 25 °C

Fig. 6. Sub-threshold drain current as a function of gate-source voltage



T_j = 25 °C

Fig. 7. Drain-source on-state resistance as a function of drain current; typical values



I_D = -8.5 A

Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values